MOSFETs Silicon N-Channel MOS (DTMOSVI)

# TK065Z65Z

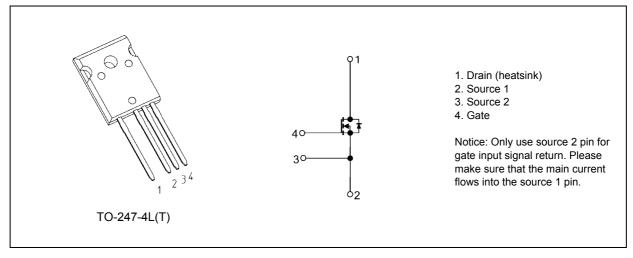
#### 1. Applications

• Switching Power Supplies

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.054 \Omega$  (typ.)
- (2) High-speed switching properties with lower capacitance.
- (3) Enhancement mode:  $V_{th}$  = 3 to 4 V ( $V_{DS}$  = 10 V,  $I_D$  = 1.69 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) ( $T_a = 25$ °C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	650	V
Gate-source voltage			V <sub>GSS</sub>	±30	1
Drain current (DC)		(Note 1)	I <sub>D</sub>	38	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	152	1
Power dissipation	(T <sub>c</sub> = 25 °C)		PD	270	W
Single-pulse avalanche energy		(Note 2)	E <sub>AS</sub>	569	mJ
Single-pulse avalanche current			I <sub>AS</sub>	9.5	Α
Reverse drain current (DC)		(Note 1)	I <sub>DR</sub>	38	1
Reverse drain current (pulsed)		(Note 1)	I <sub>DRP</sub>	152	1
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	]
Mounting torque			TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2019-03 2018-11-28

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	0.462	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	50	

Note 1: Ensure that the channel temperature does not exceed 150 °C. Note 2: V\_{DD} = 90 V, T\_{ch} = 25 °C (initial), L = 11.2 mH, I\_{AS} = 9.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

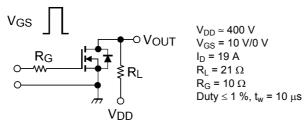
### 6. Electrical Characteristics

### 6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	$V_{DS}$ = 650 V, $V_{GS}$ = 0 V	_	_	2	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	650	_	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.69 mA	3	_	4	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 19 A		0.054	0.065	Ω

# 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS}$ = 300 V, $V_{GS}$ = 0 V, f = 100 kHz		3650	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	1		2.5	_	
Output capacitance	C <sub>oss</sub>			83	_	
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS} = 0$ to 400 V, $V_{GS} = 0$ V		148		pF
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN , f = 1 MHz	_	3	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1		25	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	60	_	
Switching time (fall time)	t <sub>f</sub>			4.2	_	
Switching time (turn-off time)	t <sub>off</sub>	1		130	_	ns
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \le V_{(BR)DSS}, I_D \le 19 A$	120	_	_	V/ns



#### Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V, I <sub>D</sub> = 38 A		62	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	18	_	
Gate-drain charge	Q <sub>gd</sub>		_	17	_	

#### 6.4. Source-Drain Characteristics ( $T_a = 25 \ ^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	$V_{DSF}$	I <sub>DR</sub> = 38 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	V <sub>DD</sub> = 400 V,		350	_	ns
Reverse recovery charge	Q <sub>rr</sub>	I <sub>DR</sub> = 19 A, V <sub>GS</sub> = 0 V -dI <sub>DR</sub> /dt = 100 A/μs	—	6	_	μC
Peak reverse recovery current	l <sub>rr</sub>		—	34	—	А
Diode dv/dt ruggedness	dv/dt	$V_{DD} \leq 400$ V, $I_{DR} \leq 19$ A, $V_{GS}$ = 0 V	50	_	_	V/ns

## 7. Marking (Note)

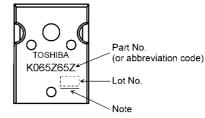


Fig. 7.1 Marking

 Note:
 A line under a Lot No. identifies the indication of product Labels.

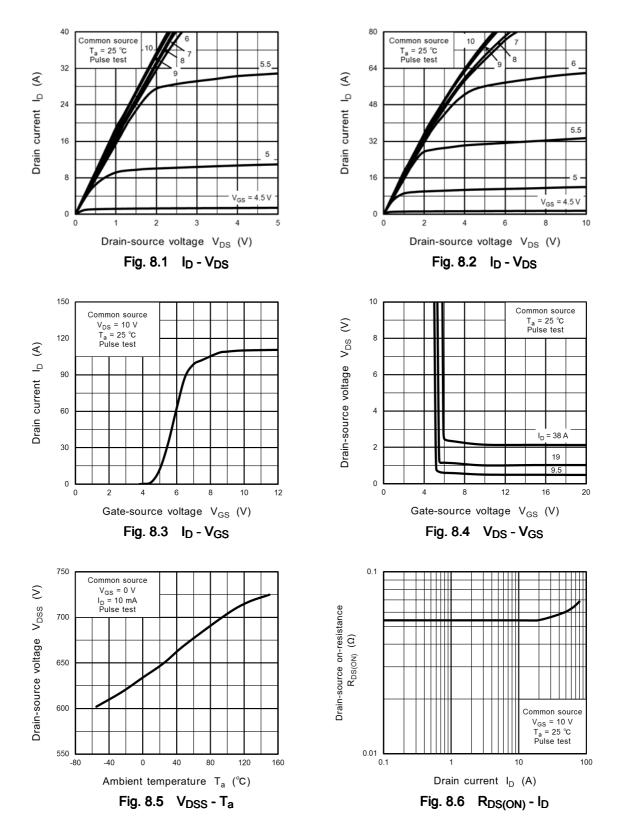
 Not underlined:
 [[Pb]]/INCLUDES > MCV

 Underlined:
 [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

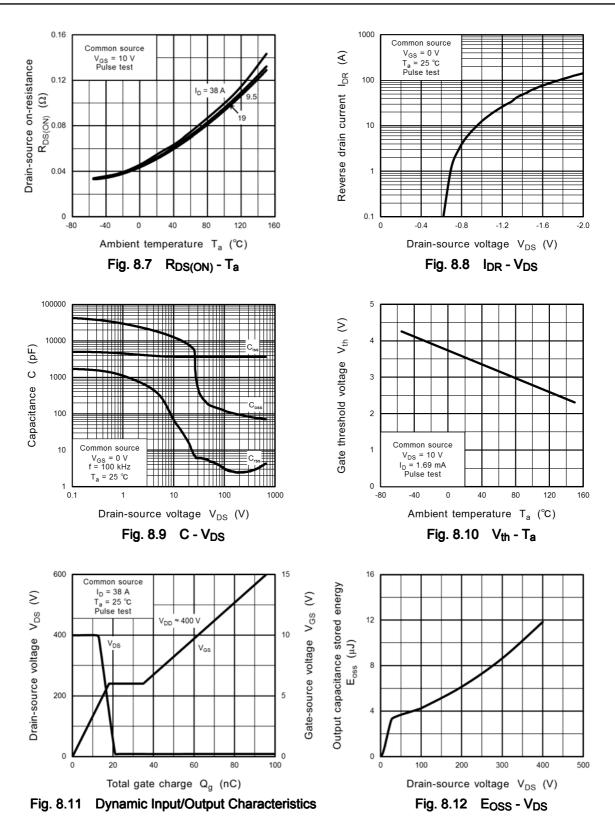
 Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

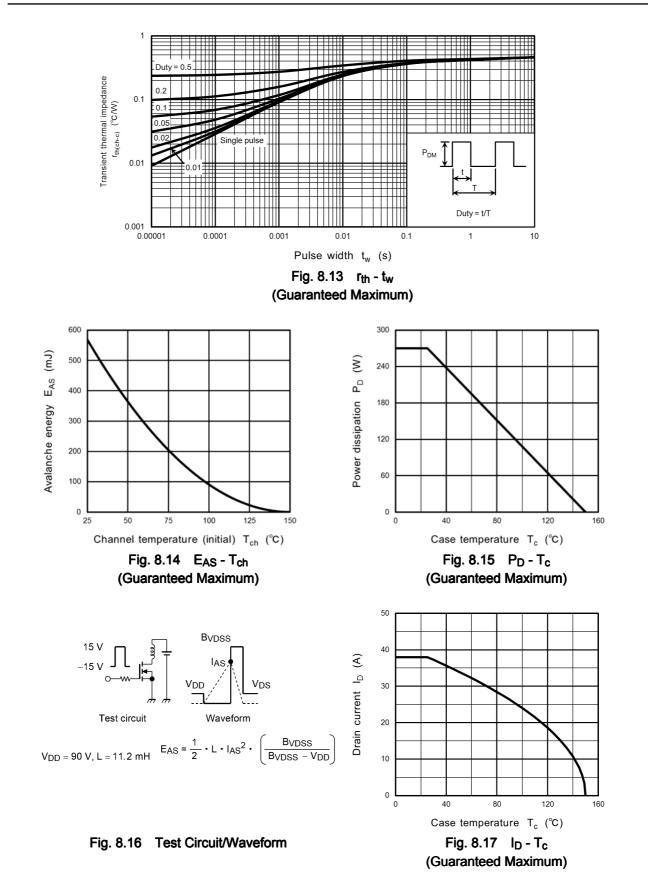
 The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

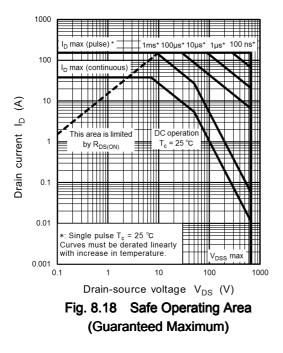
### 8. Characteristics Curves (Note)









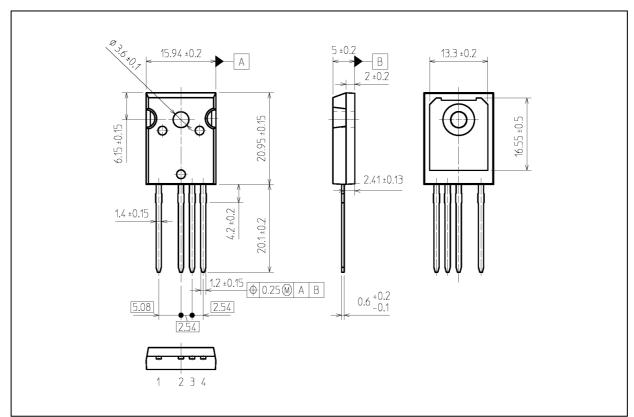


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

# TK065Z65Z

### Package Dimensions

Unit: mm



### Weight: 6.35 g (typ.)

	Package Name(s)
TOSHIBA: 2-16M2A	
Nickname: TO-247-4L(T)	

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